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A
Descrição das amostras

Abaixo são expostas a descrição das amostras utilizadas para validação dos modelos discutidos neste trabalho.

Camada	Repetição	Material	Espess.(nm)	Conc.(m^{-3})
Cap	1	$GaAs$	17	-
Camada P	1	$Al_{0,33}Ga_{0,67}As$	150	$1,3 \times 10^{(}24)$
Camada intrínseca	1	$Al_{0,33}Ga_{0,67}As$	510	-
Poços quânticos	50	$GaAs$	8.5	-
Camada N	1	$Al_{0,33}Ga_{0,67}As$	460	$1,3 \times 10^{(}24)$

Tabela A.1: Amostra G946

Camada	Repetição	Material	Espess.(nm)	Conc.(m^{-3})
Cap	1	$GaAs$	20	-
Camada P	1	$Al_{0,25}Ga_{0,75}As$	250	$7 \times 10^{(}23)$
Camada intrínseca	1	$Al_{0,35}Ga_{0,65}As$	483	-
Poços quânticos	30	$GaAs$	8.7	-
Camada N	1	$Al_{0,25}Ga_{0,75}As$	600	$2 \times 10^{(}23)$

Tabela A.2: Amostra QT76

Camada	Repetição	Material	Espess.(nm)	Conc.(m^{-3})
Cap	1	$GaAs$	40	-
Camada P	1	$Al_{0,36}Ga_{0,64}As$	150	$9 \times 10^{(}23)$
Camada intrínseca	1	$Al_{0,36}Ga_{0,64}As$	480	-
Poços quânticos	30	$GaAs$	8.4	-
Camada N	1	$Al_{0,36}Ga_{0,64}As$	600	$2,5 \times 10^{(}23)$

Tabela A.3: Amostra QT468A

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Camada	Repetição	Material	Espess.(nm)	Conc.(m^{-3})
Cap	1	$GaAs$	40	-
Camada P	1	$Al_{0,36}Ga_{0,64}As$	150	$9 \times 10^(23)$
Camada intrínseca	1	$Al_{0,36}Ga_{0,64}As$	480	-
Poços quânticos	0	-	-	-
Camada N	1	$Al_{0,36}Ga_{0,64}As$	600	$2,5 \times 10^(23)$

Tabela A.4: Amostra QT468B

Camada	Repetição	Material	Espess.(nm)	Conc.(m^{-3})
Cap	1	$GaAs$	600	-
Cap	1	$Al_{0,8}Ga_{0,2}As$	45	$2 \times 10^(24)$
Camada P	1	$Al_{0,31}Ga_{0,69}As$	500	$2 \times 10^(24)$
Camada intrínseca	1	$Al_{0,31}Ga_{0,69}As$	800	-
Poços quânticos	50	$GaAs$	10	-
Camada N	1	$Al_{0,31}Ga_{0,69}As$	500	$6 \times 10^(24)$

Tabela A.5: Amostra QT229

Camada	Repetição	Material	Espess.(nm)	Conc.(m^{-3})
Cap	1	$GaAs$	20	-
Camada P	1	$Al_{0,35}Ga_{0,65}As$	150	$9 \times 10^(23)$
Camada intrínseca	1	$Al_{0,35}Ga_{0,65}As$	310	-
Poços quânticos	1	$GaAs$	5	-
Camada N	1	$Al_{0,35}Ga_{0,65}As$	600	$2,5 \times 10^(23)$

Tabela A.6: Amostra CB501

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